

December 1992

CMOS Dual 4-Bit Latch

Features

- High-Voltage Types (20-Volt Rating)
- 3-State Outputs
- Standardized, Symmetrical Output Characteristics
- 100% Tested for Quiescent Current at 20V
- 5V, 10V, and 15V Parametric Ratings
- Maximum Input Current of $1\mu\text{A}$ at 18V Over Full Package Temperature Range; 100nA at 18V and 25°C
- Noise Margin (Full Package-Temperature Range):
 - 1V at VDD = 5V
 - 2V at VDD = 10V
 - 2.5V at VDD = 15V
- Meets all Requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications

- Digital Multiplexing
- Number-sequence Generation
- Signal Gating

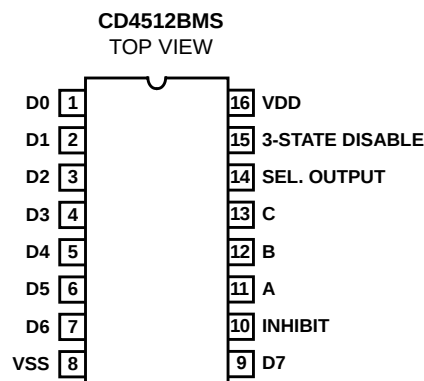
Description

CD4512BMS is an 8-channel data selector featuring a three-state output that can interface directly with, and drive, data lines of bus-oriented systems.

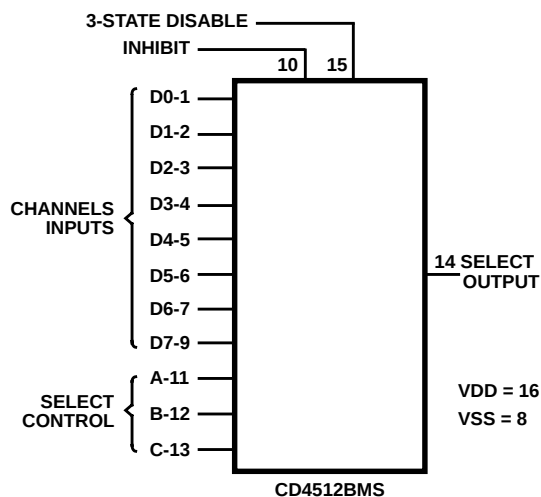
The CD4512BMS is supplied in these 16 lead outline packages:

Braze Seal DIP	H4S
Frit Seal DIP	H1E
Ceramic Flatpack	H3X

Pinout



Functional Diagram



Specifications CD4512BMS

Absolute Maximum Ratings

DC Supply Voltage Range, (VDD) -0.5V to +20V
 (Voltage Referenced to VSS Terminals)
 Input Voltage Range, All Inputs -0.5V to VDD +0.5V
 DC Input Current, Any One Input $\pm 10\mu\text{A}$
 Operating Temperature Range -55°C to +125°C
 Package Types D, F, K, H
 Storage Temperature Range (TSTG) -65°C to +150°C
 Lead Temperature (During Soldering) +265°C
 At Distance 1/16 $\pm$ 1/32 Inch (1.59mm $\pm$ 0.79mm) from case for
 10s Maximum

Reliability Information

Thermal Resistance θ_{ja} θ_{jc}
 Ceramic DIP and FRIT Package 80°C/W 20°C/W
 Flatpack Package 70°C/W 20°C/W
 Maximum Package Power Dissipation (PD) at +125°C
 For $T_A = -55^\circ\text{C}$ to +100°C (Package Type D, F, K) 500mW
 For $T_A = +100^\circ\text{C}$ to +125°C (Package Type D, F, K) Derate
 Linearity at 12mW/°C to 200mW
 Device Dissipation per Output Transistor 100mW
 For $T_A =$ Full Package Temperature Range (All Package Types)
 Junction Temperature +175°C

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS (NOTE 1)		GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
						MIN	MAX	
Supply Current	IDD	VDD = 20V, VIN = VDD or GND		1	+25°C	-	10	μA
				2	+125°C	-	1000	μA
		VDD = 18V, VIN = VDD or GND		3	-55°C	-	10	μA
Input Leakage Current	IIL	VIN = VDD or GND	VDD = 20	1	+25°C	-100	-	nA
				2	+125°C	-1000	-	nA
			VDD = 18V	3	-55°C	-100	-	nA
Input Leakage Current	IIH	VIN = VDD or GND	VDD = 20	1	+25°C	-	100	nA
				2	+125°C	-	1000	nA
			VDD = 18V	3	-55°C	-	100	nA
Output Voltage	VOL15	VDD = 15V, No Load		1, 2, 3	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH15	VDD = 15V, No Load (Note 3)		1, 2, 3	+25°C, +125°C, -55°C	14.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V		1	+25°C	0.53	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V		1	+25°C	1.4	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V		1	+25°C	3.5	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V		1	+25°C	-	-0.53	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V		1	+25°C	-	-1.8	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V		1	+25°C	-	-1.4	mA
Output Current (Source)	IOH15	VDD = 15V, VOUT = 13.5V		1	+25°C	-	-3.5	mA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10 μA		1	+25°C	-2.8	-0.7	V
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10 μA		1	+25°C	0.7	2.8	V
Functional	F	VDD = 2.8V, VIN = VDD or GND		7	+25°C	VOH > VDD/2	VOL < VDD/2	V
		VDD = 20V, VIN = VDD or GND		7	+25°C			
		VDD = 18V, VIN = VDD or GND		8A	+125°C			
		VDD = 3V, VIN = VDD or GND		8B	-55°C			
Input Voltage Low (Note 2)	VIL	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	-	1.5	V
Input Voltage High (Note 2)	VIH	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	3.5	-	V
Input Voltage Low (Note 2)	VIL	VDD = 15V, VOH > 13.5V, VOL < 1.5V		1, 2, 3	+25°C, +125°C, -55°C	-	4	V
Input Voltage High (Note 2)	VIH	VDD = 15V, VOH > 13.5V, VOL < 1.5V		1, 2, 3	+25°C, +125°C, -55°C	11	-	V
Tri-State Output Leakage	IOZL	VIN = VDD or GND VOUT = 0V	VDD = 20V	1	+25°C	-0.4	-	μA
				2	+125°C	-12	-	μA
			VDD = 18V	3	-55°C	-0.4	-	μA
Tri-State Output Leakage	IOZH	VIN = VDD or GND VOUT = VDD	VDD = 20V	1	+25°C	-	0.4	μA
				2	+125°C	-	12	μA
			VDD = 18V	3	-55°C	-	0.4	μA

NOTES: 1. All voltages referenced to device GND, 100% testing being implemented.
 2. Go/No Go test with limits applied to inputs.
 3. For accuracy, voltage is measured differentially to VDD. Limit is 0.050V max.

Specifications CD4512BMS

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Propagation Delay Inhibit to Output	TPHL1 TPLH1	VDD = 5V, VIN = VDD or GND (Note 1, 2)	9	+25°C	-	280	ns
			10, 11	+125°C, -55°C	-	378	ns
Propagation Delay "A" Select to Output	TPHL2 TPLH2	VDD = 5V, VIN = VDD or GND (Note 1, 2)	9	+25°C	-	400	ns
			10, 11	+125°C, -55°C	-	540	ns
Propagation Delay Data to Output	TPHL3 TPLH3	VDD = 5V, VIN = VDD or GND (Note 1, 2)	9	+25°C	-	360	ns
			10, 11	+125°C, -55°C	-	486	ns
Propagation Delay 3-State Disable	TPHZ TPZH	VDD = 5V, VIN = VDD or GND (Note 2, 3)	9	+25°C	-	120	ns
			10, 11	+125°C, -55°C	-	162	ns
Propagation Delay 3-State Disable	TPLZ TPZL	VDD = 5V, VIN = VDD or GND (Note 2, 3)	9	+25°C	-	120	ns
			10, 11	+125°C, -55°C	-	162	ns
Transition Time	TTHL TTLH	VDD = 5V, VIN = VDD or GND (Note 2, 3)	9	+25°C	-	200	ns
			10, 11	+125°C, -55°C	-	270	ns

NOTES:

1. All voltages referenced to device GND.
2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Supply Current	IDD	VDD = 5V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	5	μA
				+125°C	-	150	μA
		VDD = 10V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	10	μA
				+125°C	-	300	μA
		VDD = 15V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	10	μA
				+125°C	-	600	μA
Output Voltage	VOL	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOL	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	4.95	-	V
Output Voltage	VOH	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	9.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V	1, 2	+125°C	0.36	-	mA
				-55°C	0.64	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V	1, 2	+125°C	0.9	-	mA
				-55°C	1.6	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V	1, 2	+125°C	2.4	-	mA
				-55°C	4.2	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V	1, 2	+125°C	-	-0.36	mA
				-55°C	-	-0.64	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V	1, 2	+125°C	-	-1.15	mA
				-55°C	-	-2.0	mA

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TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V	1, 2	+125°C	-	-0.9	mA
				-55°C	-	-1.6	mA
Output Current (Source)	IOH15	VDD = 15V, VOUT = 13.5V	1, 2	+125°C	-	-2.4	mA
				-55°C	-	-4.2	mA
Input Voltage Low	VIL	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	-	3	V
Input Voltage High	VIH	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	+7	-	V
Propagation Delay Inhibit to Output	TPHL1 TPLH1	VDD = 10V	1, 2, 3	+25°C	-	140	ns
		VDD = 15V	1, 2, 3	+25°C	-	100	ns
Propagation Delay "A" Select to Output	TPHL2 TPLH2	VDD = 10V	1, 2, 3	+25°C	-	170	ns
		VDD = 15V	1, 2, 3	+25°C	-	120	ns
Propagation Delay Data to Output	TPHL3 TPLH3	VDD = 10V	1, 2, 3	+25°C	-	150	ns
		VDD = 15V	1, 2, 3	+25°C	-	110	ns
Propagation Delay 3-State Enable	TPHZ TPZH	VDD = 10V	1, 2, 4	+25°C	-	60	ns
		VDD = 15V	1, 2, 4	+25°C	-	40	ns
Propagation Delay 3-State Enable	TPLZ TPZL	VDD = 10V	1, 2, 4	+25°C	-	60	ns
		VDD = 15V	1, 2, 4	+25°C	-	40	ns
Transition Time	TTHL TTLH	VDD = 10V	1, 2, 3	+25°C	-	100	ns
		VDD = 15V	1, 2, 3	+25°C	-	80	ns
Input Capacitance	CIN	Any Input	1, 2	+25°C	-	7.5	pF

NOTES:

1. All voltages referenced to device GND.
2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.
4. CL = 50pF, RL = 1K, Input TR, TF < 20ns.

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1, 4	+25°C	-	25	μA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10μA	1, 4	+25°C	-2.8	-0.2	V
N Threshold Voltage Delta	ΔVTN	VDD = 10V, ISS = -10μA	1, 4	+25°C	-	±1	V
P Threshold Voltage	VTP	VSS = 0V, IDD = 10μA	1, 4	+25°C	0.2	2.8	V
P Threshold Voltage Delta	ΔVTP	VSS = 0V, IDD = 10μA	1, 4	+25°C	-	±1	V
Functional	F	VDD = 18V, VIN = VDD or GND	1	+25°C	VOH > VDD/2	VOL < VDD/2	V
		VDD = 3V, VIN = VDD or GND					
Propagation Delay Time	TPHL TPLH	VDD = 5V	1, 2, 3, 4	+25°C	-	1.35 x +25°C Limit	ns

NOTES: 1. All voltages referenced to device GND.

2. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

3. See Table 2 for +25°C limit.

4. Read and Record

Specifications CD4512BMS

TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS +25°C

PARAMETER	SYMBOL	DELTA LIMIT
Supply Current - MSI-2	IDD	± 1.0μA
Output Current (Sink)	IOL5	± 20% x Pre-Test Reading
Output Current (Source)	IOH5A	± 20% x Pre-Test Reading

TABLE 6. APPLICABLE SUBGROUPS

CONFORMANCE GROUP		MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Initial Test (Pre Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 1 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 2 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)		100% 5004	1, 7, 9, Deltas	
Interim Test 3 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)		100% 5004	1, 7, 9, Deltas	
Final Test		100% 5004	2, 3, 8A, 8B, 10, 11	
Group A		Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11	
Group B	Subgroup B-5	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas	Subgroups 1, 2, 3, 9, 10, 11
	Subgroup B-6	Sample 5005	1, 7, 9	
Group D		Sample 5005	1, 2, 3, 8A, 8B, 9	Subgroups 1, 2 3

NOTE: 1. 5% Parametric, 3% Functional; Cumulative for Static 1 and 2.

TABLE 7. TOTAL DOSE IRRADIATION

CONFORMANCE GROUPS	MIL-STD-883 METHOD	TEST		READ AND RECORD	
		PRE-IRRAD	POST-IRRAD	PRE-IRRAD	POST-IRRAD
Group E Subgroup 2	5005	1, 7, 9	Table 4	1, 9	Table 4

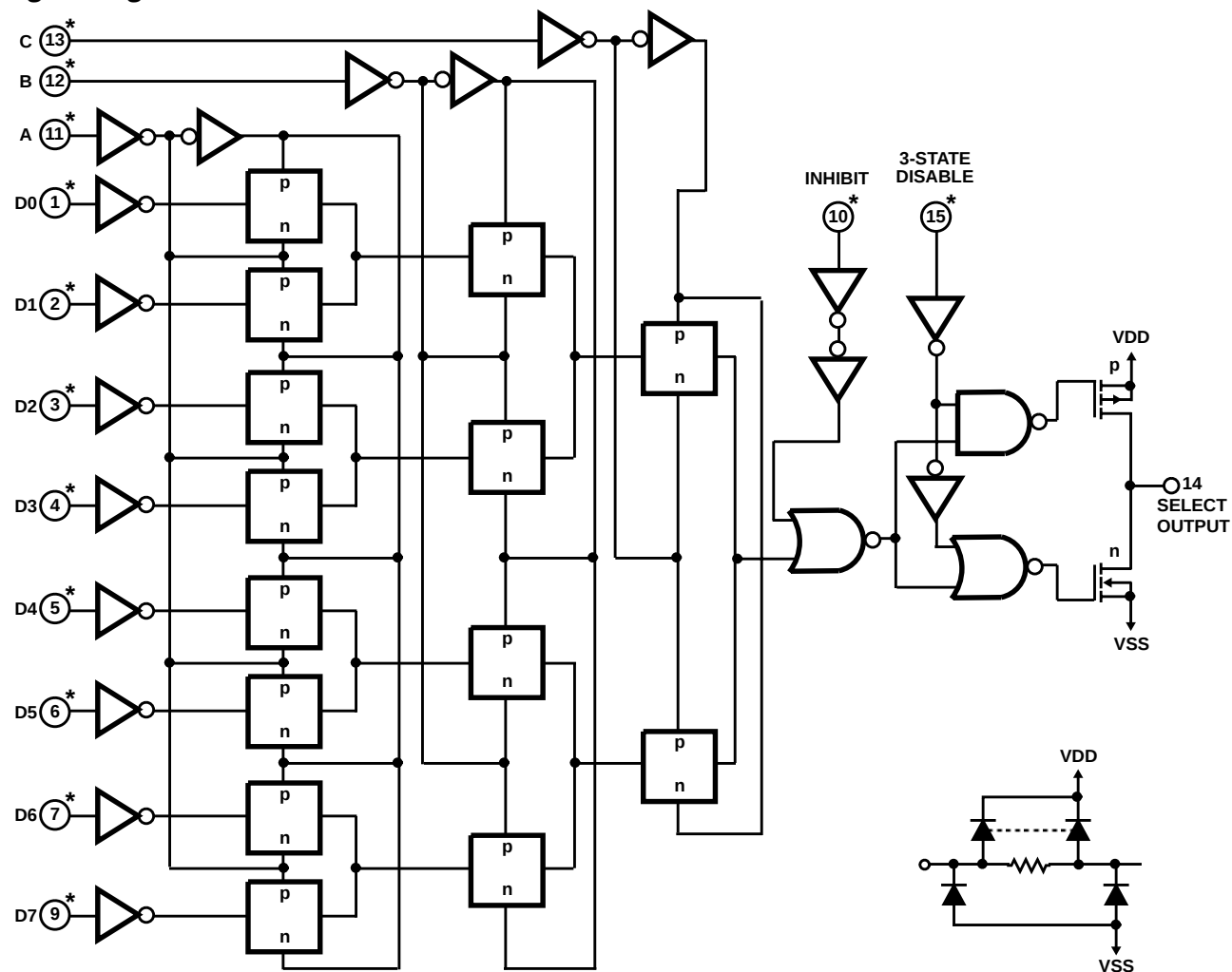
TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

FUNCTION	OPEN	GROUND	VDD	9V ± -0.5V	OSCILLATOR	
					50kHz	25kHz
Static Burn-In 1 Note 1	14	1-13, 15	16			
Static Burn-In 2 Note 1	14	8	1-7, 9-13, 15, 16			
Dynamic Burn-In Note 1	-	8, 10, 15	16	14	1-7, 9, 11, 12	13
Irradiation Note 2						

NOTES:

- Each pin except VDD and GND will have a series resistor of 10K ± 5%, VDD = 18V ± 0.5V
- Each pin except VDD and GND will have a series resistor of 47K ± 5%; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures, VDD = 10V ± 0.5V

Logic Diagram



* All inputs protected by CMOS protection network.

FIGURE 1. LOGIC DIAGRAM
TRUTH TABLE

SELECT CONT.			INH	3-STATE DISABLE	SELECT OUTPUT
A	B	C			
0	0	0	0	0	D0
1	0	0	0	0	D1
0	1	0	0	0	D2
1	1	0	0	0	D3
0	0	1	0	0	D4
1	0	1	0	0	D5
0	1	1	0	0	D6
1	1	1	0	0	D7
X	X	X	1	0	0
X	X	X	X	1	High Z

1 = HIGH LEVEL
0 = LOW LEVEL

X = DON'T CARE

Typical Performance Characteristics

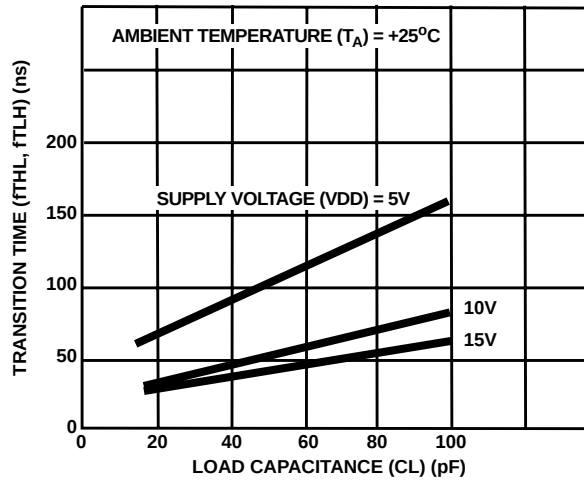


FIGURE 2. TYPICAL TRANSITION TIME AS A FUNCTION OF LOAD CAPACITANCE

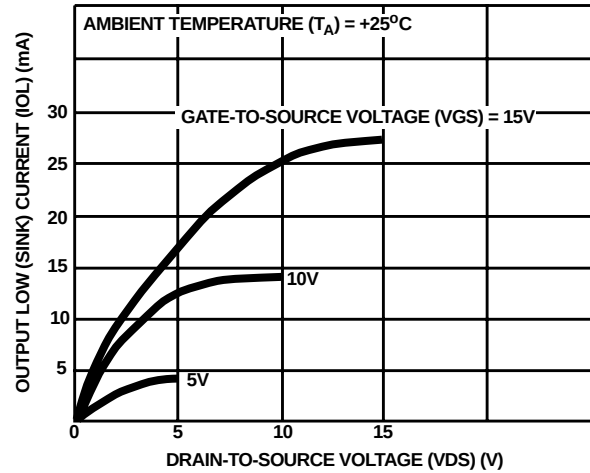


FIGURE 3. TYPICAL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

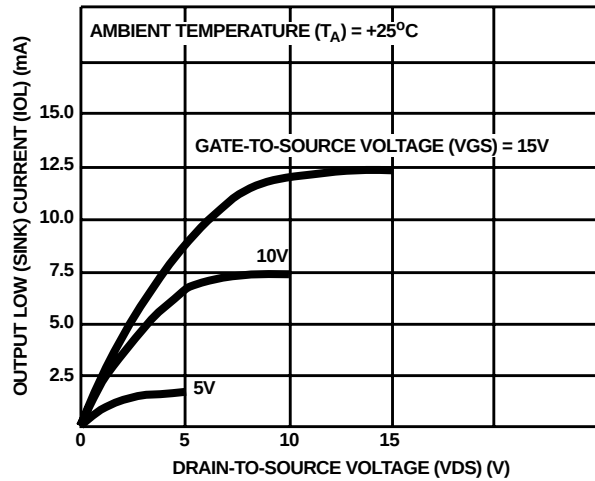


FIGURE 4. MINIMUM OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

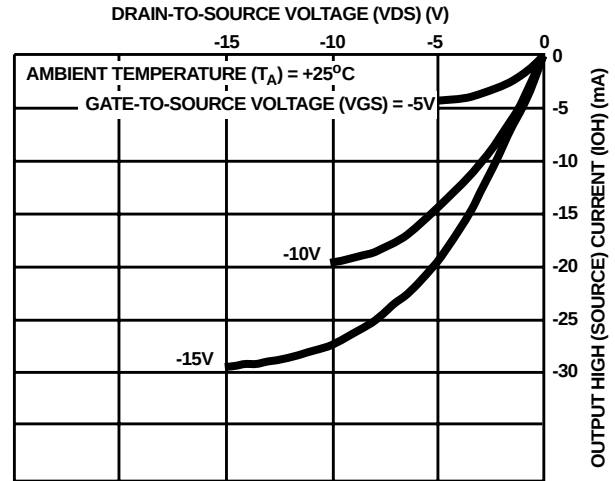


FIGURE 5. TYPICAL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

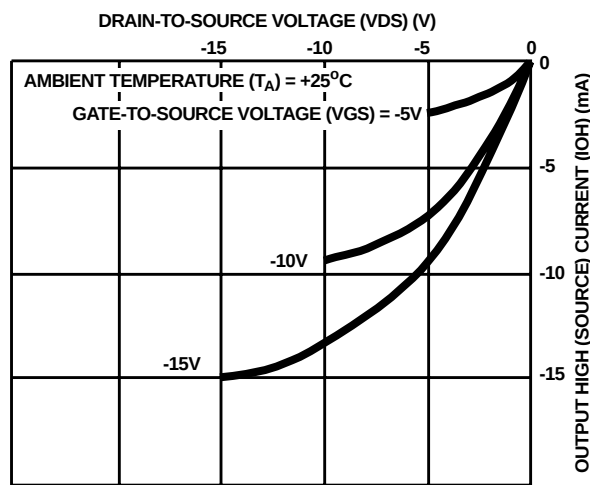


FIGURE 6. MINIMUM OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

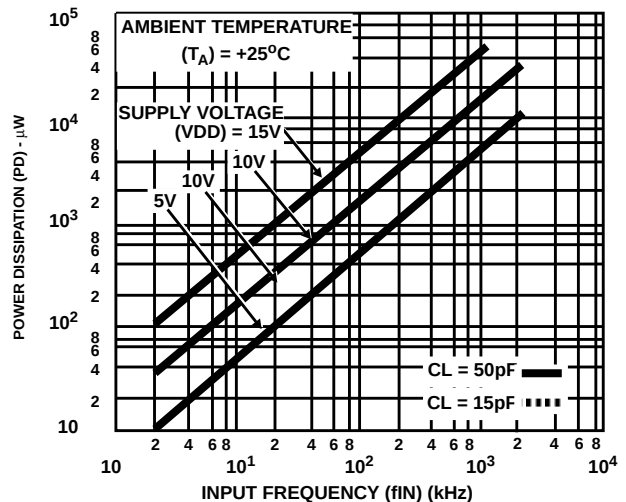


FIGURE 7. TYPICAL DYNAMIC POWER DISSIPATION AS A FUNCTION OF FREQUENCY

Typical Performance Characteristics (Continued)

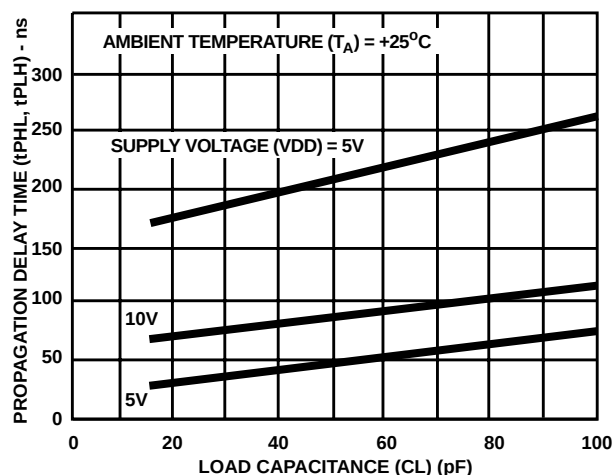
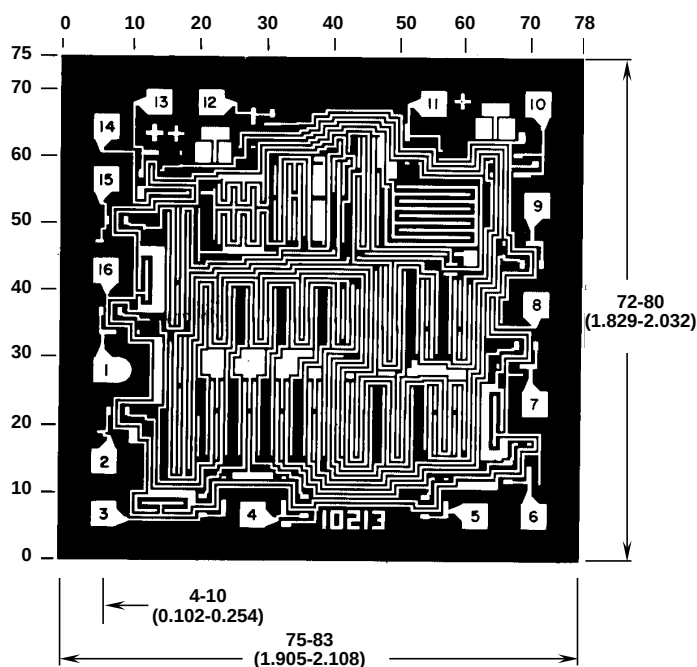


FIGURE 8. TYPICAL PROPAGATION DELAY TIME AS A FUNCTION OF LOAD CAPACITANCE ("A" SELECT TO OUTPUT)

Chip Dimensions and Pad Layouts



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch.)

METALLIZATION: Thickness: $11\text{k}\text{\AA} - 14\text{k}\text{\AA}$, AL.
PASSIVATION: $10.4\text{k}\text{\AA} - 15.6\text{k}\text{\AA}$, Silane
BOND PADS: 0.004 inches X 0.004 inches MIN
DIE THICKNESS: 0.0198 inches - 0.0218 inches